

Data Sheet

FEATURES

Extreme high temperature operation Specified temperature range -55°C to +210°C (16-lead FLATPACK) -55°C to +175°C (16-lead TSSOP) 3.0 V to 5.5 V single supply ±2.5 V dual supply 10 Ω on resistance, maximum 2 Ω on-resistance flatness, maximum 12 ns switching times Single 8:1 multiplexer Low power consumption TTL-/CMOS-compatible inputs

APPLICATIONS

Downhole drilling and instrumentation Avionics Heavy industrial High temperature environments

GENERAL DESCRIPTION

The ADG798 is a low voltage, CMOS, analog multiplexer designed to operate at very high temperatures up to 210°C. The ADG798 switches one of eight inputs (S1 to S8) to a common output, D, as determined by the 3-bit binary address lines A0, A1, and A2. An EN input on the device enables or disables the device. When the device is disabled, all channels are switched off.

The ADG798 features low power consumption and a 3.3 V to 5.5 V operating supply range. All channels exhibit break-beforemake switching action, preventing momentary shorting when switching channels. These switches are designed with an enhanced submicron process that provides low power dissipation, high switching speed, and very low on resistance.

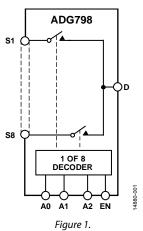
The on resistance (R_{ON}) is a maximum of 10 Ω and is closely matched between switches and very flat over the full signal range. The ADG798 operates equally well as either a multiplexer or a demultiplexer and has an input signal range that extends to the supplies.

This mux is available in a 16-lead ceramic flat package (FLATPACK) and a 16-lead ceramic flat package with reverse formed gullwing leads (FLATPACK_RF). Both of the flat

High Temperature, Low Voltage 8-Channel Multiplexer

ADG798

FUNCTIONAL BLOCK DIAGRAM



packages have an operating temperature range of -55° C to $+210^{\circ}$ C. A 16-lead TSSOP package is also available that has an operating temperature range of -55° C to $+175^{\circ}$ C. All packages are designed for robustness at extreme temperatures, and are qualified for 1000 hours of continuous operation at the maximum temperature rating.

The ADG798 is a member of a growing series of high temperature qualified products offered by Analog Devices, Inc. For a complete selection table of available high temperature products, see the high temperature product list and qualification data available at http://www.analog.com/hightemp.

PRODUCT HIGHLIGHTS

- Single-Supply/Dual-Supply Operation. The ADG798 is fully specified and guaranteed with 3.3 V and 5 V single-supply rails and ±2.5 V dual-supply rails.
- 2. Low $R_{ON}.$ The R_{ON} of the ADG798 is specified at 5 $\Omega,$ typical, at 210°C.
- 3. Low Power Consumption. The power consumption of the ADG798 is specified at ${<}0.01~\mu\text{W}.$
- 4. Guaranteed Break-Before-Make Switching Action.

Rev. A

Document Feedback

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REVISION HISTORY

6/2018-Rev. 0 to Rev. A

Added TSSOP PackageUnive	ersal
Changes to Features	1
Changes to General Description	1
Changes to Specifications, Table 1	3
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Added TSSOP Operating Temperature Range and Junction	
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Added RU-16 Thermal Characteristics, Table 6	
Changes to Figure 2 Caption	

9/2016—Revision 0: Initial Version

SPECIFICATIONS

 $V_{DD} = 5 V \pm 10\%$, $V_{SS} = 0 V$, GND = 0 V, unless otherwise noted. TSSOP temperature range = $-55^{\circ}C \le T_A \le +175^{\circ}C$ and FLATPACK temperature range = $-55^{\circ}C \le T_A \le +210^{\circ}C$, unless otherwise noted.

Table 1.

				TSSOP			FLATPAC	(
Parameter	Symbol	Test Conditions/Comments ¹	Min	Typ ²	Max	Min		Max	Unit
ANALOG SWITCH									
Analog Signal Range			0		V_{DD}	0		V_{DD}	V
On Resistance	Ron	$V_s = 0 V$ to V_{DD} , $I_{DS} = 10 mA$; see Figure 24		4.5	9		5	10	Ω
Matching Between Channels	ΔR _{ON}	$V_{\text{S}} = 0 \text{ V} \text{ to } V_{\text{DD}}, I_{\text{DS}} = 10 \text{ mA}$		0.6	1.2		1.25	1.5	Ω
Flatness	RFLAT (ON)	$V_{\text{S}} = 0 \text{ V to } V_{\text{DD}}$, $I_{\text{DS}} = 10 \text{ mA}$			1.5		0.75	2	Ω
LEAKAGE CURRENTS		$V_{DD} = 5.5 V$							
Source Off Leakage	Is (Off)	$V_D = 4.5 V/1 V$, $V_S = 1 V/4.5 V$; see Figure 25	-50	±0.01	+50	-180	±0.01	+180	nA
Drain Off Leakage	I _D (Off)	$V_D = 4.5 V/1 V, V_S = 1 V/4.5 V;$ see Figure 26	-650	±0.01	+650	-2600	±0.01	+2600	nA
Channel On Leakage	I _D (On), Is (On)	$V_D = V_S = 1 V$ or 4.5 V; see Figure 27	-650	±0.01	+650	-2600	±0.01	+2600	nA
DIGITAL INPUTS									
Input Voltage									
High	VINH		2.4			2.4			v
Low	VINL				0.8			0.8	v
Input Current	I _{INL} or I _{INH}	$V_{\text{IN}} = V_{\text{INL}} \text{ or } V_{\text{INH}}$	-800	+0.005	+800	-800	+0.005	+800	nA
Digital Input Capacitance	CIN			2			2		рF
DYNAMIC CHARACTERISTICS ³									
Transition Time	transition	R_L = 150 Ω,C_L = 15 pF; see Figure 28		12	21		12	23	ns
		$V_{S1} = 3 V/0 V, V_{S8} = 0 V/3 V$							
Break-Before-Make Time Delay	topen	$\label{eq:RL} \begin{split} R_L &= 150 \ \Omega, \ C_L = 15 \ p\text{F}, \ V_S = 3 \ V; \\ see \ Figure \ 29 \end{split}$	1	8		1	8		ns
		T _A = maximum temperature		9			9		ns
On Time	t _{on} (EN)	$R_L = 150 \ \Omega, C_L = 15 \ pF$ V _s = 3 V; see Figure 30		11	17		11	20	ns
OffTime	t _{off} (EN)	$R_L = 150 \Omega$, $C_L = 15 pF$ $V_S = 3 V$; see Figure 30		5.5	11		5.5	12	ns
Charge Injection	Qinj	$V_s = 2.5 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 31		±3			±3		рC
Off Isolation		$R_L = 50 \Omega, C_L = 5 pF, f = 10 MHz$		-60			-60		dB
		$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 32		-80			-80		dB
Channel to Channel Crosstalk		$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$		-60			-60		dB
		R_L = 50 $\Omega,$ C_L = 5 pF, f = 1 MHz; see Figure 33		-80			-80		dB
–3 dB Bandwidth		$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 34		55			55		MH
Source Capacitance, Off	Cs (Off)	f = 1 MHz		13			13		рF

			TSSOP FLATPA		FLATPAC	K			
Parameter	Symbol	Test Conditions/Comments ¹	Min	Typ ²	Max	Min	Typ ²	Max	Unit
Drain Capacitance, Off	C _D (Off)	f = 1 MHz		85			85		рF
Source/Drain Capacitance,	C _D (On),	f = 1 MHz		96			96		рF
On	Cs (On)								
POWER REQUIREMENTS		$V_{DD} = 5.5 V$							
Supply Current	I _{DD}	Digital inputs = 0 V or 5.5 V		5	35		40	70	μΑ

¹ The ADG798 is qualified for a minimum of 1000 hours of continuous operation at the maximum temperature rating. ² $T_A = 25^{\circ}$ C, except for the analog switch and power requirements values where $T_A = 175^{\circ}$ C (TSSOP only) or 210°C (FLATPACK only). ³ Guaranteed by design, not subject to production test.

Data Sheet

 $V_{DD} = 3.3 \text{ V} \pm 10\%$, $V_{SS} = 0 \text{ V}$, GND = 0 V, unless otherwise noted. TSSOP temperature range = $-55^{\circ}C \le T_A \le +175^{\circ}C$ and FLATPACK temperature range = $-55^{\circ}C \le T_A \le +210^{\circ}C$, unless otherwise noted.

				TSSOP			FLATPACI	(
Parameter	Symbol	Test Conditions/Comments ¹	Min	Typ ²	Мах	Min		Max	Unit
ANALOG SWITCH									
Analog Signal Range			0		V_{DD}	0 V		V_{DD}	V
On Resistance	R _{ON}	$V_s = 0 V$ to V_{DD} , $I_{Ds} = 10 mA$; see Figure 24		7	15		8	20	Ω
Matching Between Channels	ΔR_{ON}	$V_{\text{S}}=0VtoV_{\text{DD}}, I_{\text{DS}}=10\text{mA}$		0.4	1.2		0.5	1.5	Ω
Flatness	RFLAT (ON)	$V_s = 0 V$ to V_{DD} , $I_{Ds} = 10 \text{ mA}$		2.5	3.5		3	4.5	Ω
LEAKAGE CURRENTS		$V_{DD} = 3.63 V$							
Source Off Leakage	I _s (Off)	$V_D = 2.3 \text{ V}/1 \text{ V}, \text{ V}_S = 1 \text{ V}/2.3 \text{ V}; \text{ see}$ Figure 25	-50	±0.01	+50	-180	±0.01	+180	nA
Drain Off Leakage	I _D (Off)	$V_D = 2.3 \text{ V/1 V}, V_S = 1 \text{ V/2.3 V};$ see Figure 26	-650	±0.01	+650	-2600	±0.01	+2600	nA
Channel On Leakage	I _D (On), Is (On)	$V_D = V_S = 1 V \text{ or } 2.3 V; \text{ see}$ Figure 27	-650	±0.01	+650	-2600	±0.01	+2600	nA
DIGITAL INPUTS									
Input Voltage									
High	VINH		2.4			2.0			V
Low	VINL				0.8			0.8	V
Input Current	l _{inl} or I _{inh}	$V_{\text{IN}} = V_{\text{INL}} \text{ or } V_{\text{INH}}$	-800	+0.005	+800	-800	+0.005	+800	nA
Digital Input Capacitance	CIN			2			2		pF
DYNAMIC CHARACTERISTICS ³									
Transition Time	t transition	R∟ = 150 Ω, C∟ = 15 pF; see Figure 28		18	34		18	38	ns
		$V_{S1} = 2 V/0 V, V_{S8} = 0 V/2 V$							
Break-Before-Make Time Delay	t _{open}	$R_L = 150 \Omega$, $C_L = 15 pF$, $V_S = 2 V$; see Figure 29	1	10		1	10		ns
		T _A = maximum temperature		15			15		ns
On Time	t _{on} (EN)	$R_L = 150 \Omega$, $C_L = 15 pF$ $V_S = 2 V$; see Figure 30		14	26		14	28	ns
Off Time	t _{off} (EN)	$R_L = 150 \Omega$, $C_L = 15 pF$ V _s = 2 V; see Figure 30		8.5	16		8.5	17	ns
Charge Injection	Q _{INJ}	$V_s = 1.5 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 31		±3			±3		рC
Off Isolation		$R_L = 50 \Omega, C_L = 5 pF, f = 10 MHz$		-60			-60		dB
		$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 32		-80			-80		dB
Channel to Channel Crosstalk		$R_L = 50 \Omega, C_L = 5 pF, f = 10 MHz$		-60			-60		dB
		$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 33		-80			-80		dB
–3 dB Bandwidth		$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 34		55			55		MHz
Source Capacitance, Off	Cs (Off)	f = 1 MHz		13			13		pF
Drain Capacitance, Off	C _D (Off)	f = 1 MHz		85			85		pF
Source/Drain Capacitance, On	C _D (On), C _s (On)	f = 1 MHz		96			96		pF

			TSSOP FLATPA		FLATPAC	К			
Parameter	Symbol	Test Conditions/Comments ¹	Min	Typ ²	Max	Min	Typ ²	Max	Unit
POWER REQUIREMENTS	V _{DD} = 3.63 V								
Supply Current	I _{DD}	Digital inputs = 0 V or 3.63 V		5	35		40	70	μA

¹ The ADG798 is qualified for a minimum of 1000 hours of continuous operation at the maximum temperature rating. ² $T_A = 25^{\circ}$ C, except for the analog switch and power requirements values where $T_A = 175^{\circ}$ C (TSSOP only) or 210°C (FLATPACK only). ³ Guaranteed by design, not subject to production test.

DUAL SUPPLY

 $V_{DD} = 2.5 \text{ V} \pm 10\%, V_{SS} = -2.5 \text{ V} \pm 10\%, \text{ GND} = 0 \text{ V}, \text{ unless otherwise noted. TSSOP temperature range} = -55^{\circ}\text{C} \le T_{A} \le +175^{\circ}\text{C} \text{ and FLATPACK temperature range} = -55^{\circ}\text{C} \le T_{A} \le +210^{\circ}\text{C}, \text{ unless otherwise noted.}$

Table 3.

			TSSOP				FLATPAC	(
Parameter	Symbol	Test Conditions/Comments ¹	Min	Typ ²	Max	Min		Max	Unit
ANALOG SWITCH									
Analog Signal Range			0		V_{DD}	Vss		V_{DD}	V
On Resistance	Ron	$V_s = V_{ss}$ to V_{DD} , $I_{Ds} = 10$ mA; see Figure 24		4.5	9		5	10	Ω
Matching Between Channels	ΔR _{ON}	$V_{\text{S}} = V_{\text{SS}} \text{ to } V_{\text{DD}}, I_{\text{DS}} = 10 \text{ mA}$		0.6	1.2		1.25	1.5	Ω
Flatness	RFLAT (ON)	$V_{S} = V_{SS}$ to V_{DD} , $I_{DS} = 10$ mA			1.5		0.6	2	Ω
LEAKAGE CURRENTS		$V_{DD} = +2.75 \text{ V}, \text{V}_{\text{S}} = -2.75 \text{ V}$							
Source Off Leakage	Is (Off)	$V_s = +2.25 V/-1.25 V, V_D =$ -1.25 V/+2.25 V; see Figure 25	-50	±0.01	+50	-180	±0.01	+180	nA
Drain Off Leakage	I⊳ (Off)	$V_s = +2.25 V/-1.25 V, V_D =$ -1.25 V/+2.25 V; see Figure 26	-650	±0.01	+650	-2600	±0.01	+2600	nA
Channel On Leakage	I _D (On), Is (On)	$V_D = V_S = -1.25 \text{ V/+}2.25 \text{ V}$; see Figure 27	-650	±0.01	+650	-2600	±0.01	+2600	nA
DIGITAL INPUTS									
Input Voltage									
High	V _{INH}		2.4			2.0			V
Low	VINL				0.8			0.8	V
Input Current	IINL OR IINH	$V_{\text{IN}} = V_{\text{INL}} \text{ or } V_{\text{INH}}$	-800	+0.005	+800	-800	+0.005	+800	nA
Digital Input Capacitance	CIN			2			2		pF
DYNAMIC CHARACTERISTICS ³									
Transition Time	t TRANSITION	$R_L = 150 \Omega$, $C_L = 15 pF$; see Figure 28		18	28		14	30	ns
		$V_{S1} = 1.5 \text{ V/O V}, V_{S8} = 0 \text{ V/1.5 V}$							
Break-Before-Make Time Delay	topen	$\label{eq:RL} \begin{split} R_L &= 150 \; \Omega, C_L = 15 \; pF, V_S = 2 \; V; \\ see \; Figure \; 29 \end{split}$	1	10		1	10		ns
		T _A = maximum temperature		13			13		ns
On Time	ton (EN)	$R_L = 150 \Omega$, $C_L = 15 pF$ $V_s = 2 V$; see Figure 30		19	28		19	30	ns
Off Time	toff (EN)	$R_L = 150 \Omega, C_L = 15 pF$ V _s = 2 V; see Figure 30		11.5	19		11.5	20	ns
Charge Injection	QINJ	$V_s = 0 V$, $R_s = 0 \Omega$, $C_L = 1 nF$; see Figure 31		±3			±3		рC
Off Isolation		$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$		-60			-60		dB
		$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 32		-80			-80		dB
Channel to Channel Crosstalk		$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$		-60			-60		dB
		$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 33		-80			-80		dB
–3 dB Bandwidth		$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 34		55			55		MH
Source Capacitance, Off	C _s (Off)	f = 1 MHz		13			13		pF

				TSSOP			FLATPAC	:K	
Parameter	Symbol	Test Conditions/Comments ¹	Min	Typ ²	Max	Min	Typ ²	Max	Unit
Drain Capacitance, Off	C _D (Off)	f = 1 MHz		85			85		pF
Source/Drain Capacitance, On	C _D (On), C _S (On)	f = 1 MHz		96			96		pF
POWER REQUIREMENTS		$V_{DD} = 2.75 V$							
Supply Current	IDD	Digital inputs = 0 V or 2.75 V		5	35		40	70	μΑ
	lss	$V_{ss} = -2.75$ V; digital inputs = 0 V or 2.75 V		5	35		40	70	μΑ

¹ The ADG798 is qualified for a minimum of 1000 hours of continuous operation at the maximum temperature rating. ² $T_A = 25^{\circ}$ C, except for the analog switch and power requirements values where $T_A = 175^{\circ}$ C (TSSOP) or 210°C (FLATPACK).

³ Guaranteed by design, not subject to production test.

CONTINUOUS CURRENT PER CHANNEL, Sx OR D

Table 4.

Parameter	175°C	210°C	Unit
CONTINUOUS CURRENT, Sx OR D			
FLATPACK $\theta_{JA} = 70^{\circ}$ C/W			
$V_{DD} = 5 V, V_{SS} = 0 V$	30	30	mA maximum
$V_{DD} = 3 V, V_{SS} = 0 V$	30	30	mA maximum
$V_{DD} = +2.5 V, V_{SS} = -2.5 V$	30	30	mA maximum
TSSOP $\theta_{JA} = 109.6^{\circ}C/W$			
$V_{DD} = 5 V, V_{SS} = 0 V$	30		mA maximum
$V_{DD} = 3 V, V_{SS} = 0 V$	30		mA maximum
$V_{DD} = +2.5 V, V_{SS} = -2.5 V$	30		mA maximum

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}$ C, unless otherwise noted.

Tabl	e 5.

Table 5.	
Parameter	Rating
V _{DD} to V _{SS}	7 V
V _{DD} to GND	–0.3 V to +7 V
Vss to GND	+0.3 V to -3.5 V
Analog Inputs ¹	$\label{eq:Vss} \begin{array}{l} V_{ss} - 0.3 \: V \: to \: V_{\text{DD}} + 0.3 \: V \\ or \: 30 \: mA, \: whichever \\ occurs \: first \end{array}$
Digital Inputs ¹	-0.3 V to V _{DD} + 0.3 V or 30 mA, whichever occurs first
Peak Current, Sx or D (Pulsed at 1 ms, 10% Duty Cycle Maximum)	94.9 mA
Continuous Current, Sx or D ²	Data + 5%
Operating Temperature Range	
TSSOP	–55°C to +175°C
FLATPACK	-55°C to +210°C
Junction Temperature	
TSSOP	180°C
FLATPACK	211°C

¹ Overvoltages at Ax, EN, Sx, or D are clamped by internal codes. Limit the current to the maximum ratings given.

² See Table 4.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

Only one absolute maximum rating can be applied at any one time.

THERMAL RESISTANCE

Thermal performance is directly linked to PCB design and operating environment. Close attention to PCB thermal design is required.

Table 6. Thermal Resistance

Package Type ¹	θ」Α	οις	Unit
F-16-1	70	22	°C/W
FR-16-1	70	10	°C/W
RU-16	109.6	36.5	°C/W

¹ Thermal impedance simulated values are based on a JEDEC 2s2p thermal test board. See JEDEC JESD51.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

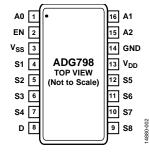


Figure 2. TSSOP and FLATPACK Pin Configuration

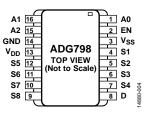


Figure 3. Reversed Formed FLATPACK Pin Configuration

Table 7. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	A0	Digital Input. This pin controls the configuration of the switch, as shown in the truth table (see Table 8).
2	EN	Digital Input. This pin controls the configuration of the switch, as shown in the truth table (see Table 8).
3	Vss	Most Negative Power Supply Pin in Dual-Supply Applications. For single-supply applications, tie this pin to GND.
4	S1	Source Terminal. This pin can be an input or output.
5	S2	Source Terminal. This pin can be an input or output.
6	S3	Source Terminal. This pin can be an input or output.
7	S4	Source Terminal. This pin can be an input or output.
8	D	Drain Terminal. This pin can be an input or output.
9	S8	Source Terminal. This pin can be an input or output.
10	S7	Source Terminal. This pin can be an input or output.
11	S6	Source Terminal. This pin can be an input or output.
12	S5	Source Terminal. This pin can be an input or output.
13	V _{DD}	Most Positive Power Supply Pin.
14	GND	Ground (0 V) Reference.
15	A2	Digital Input. This pin controls the configuration of the switch, as shown in the truth table (see Table 8).
16	A1	Digital Input. This pin controls the configuration of the switch, as shown in the truth table (see Table 8).

TRUTH TABLE

Table 8. Truth Table

A2	A1	AO	EN	Switch Condition	
X ¹	X ¹	X ¹	0	None	
0	0	0	1	S1	
0	0	1	1	S2	
0	1	0	1	S3	
0	1	1	1	S4	
1	0	0	1	S5	
1	0	1	1	S6	
1	1	0	1	S7	
1	1	1	1	S8	

¹ X means don't care.

TYPICAL PERFORMANCE CHARACTERISTICS

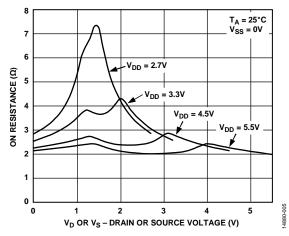


Figure 4. On Resistance as a Function of V_D (V_s) for Single Supply

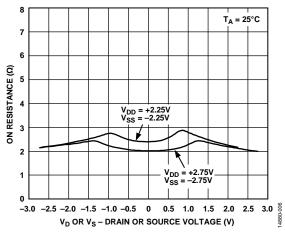


Figure 5. On Resistance as a Function of V_D (V_s) for Dual Supply

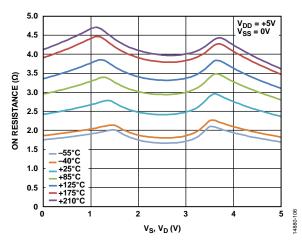


Figure 6. On Resistance as a Function of $V_{S_r} V_D$ for Different Temperatures, 5 V Single Supply

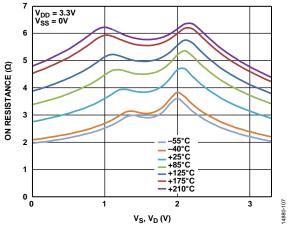


Figure 7. On Resistance as a Function of $V_{\rm S}$ ($V_{\rm D}$) for Different Temperatures, 3.3 V Single Supply

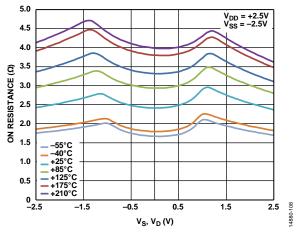


Figure 8. On Resistance as a Function of Vs (Vb) for Different Temperatures, ± 2.5 V Dual Supply

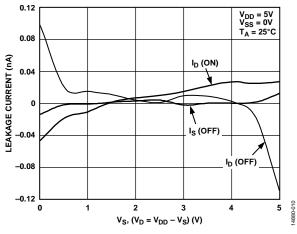


Figure 9. Leakage Current as a Function of V_D (V_s)

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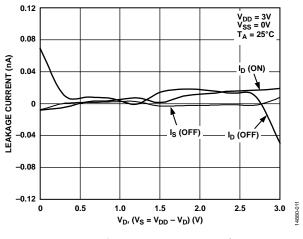
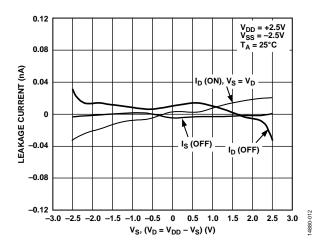
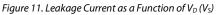


Figure 10. Leakage Current as a Function of V_D (V_S)





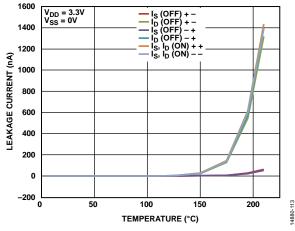


Figure 12. Leakage Current as a Function of Temperature, $V_{DD} = 3.3 V$, $V_{SS} = 0 V$

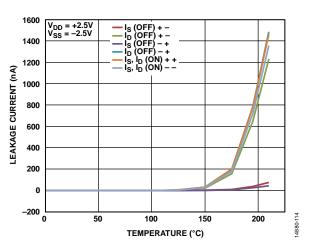


Figure 13. Leakage Current as a Function of Temperature, V_{DD} = +2.5 V, V_{SS} = -2.5 V

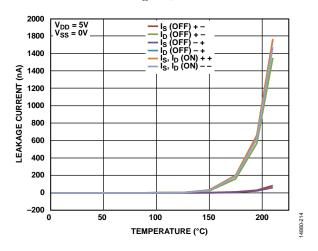


Figure 14. Leakage Current vs. Temperature, $V_{DD} = 5 V$

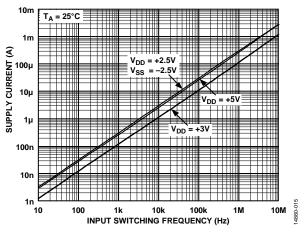


Figure 15. Supply Current vs. Input Switching Frequency

Data Sheet

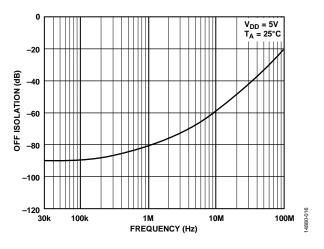
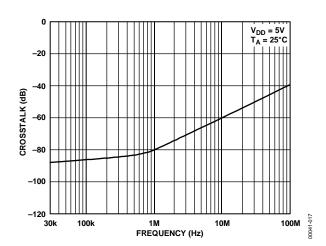


Figure 16. Off Isolation vs. Frequency





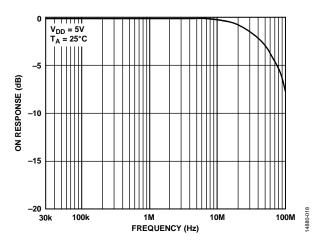


Figure 18. On Response vs. Frequency

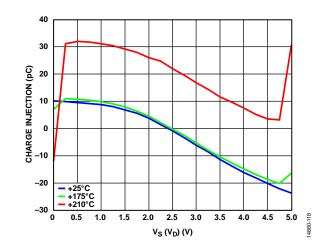


Figure 19. Charge Injection as a Function of V_S (V_D) for Various Temperatures, 5 V Single Supply

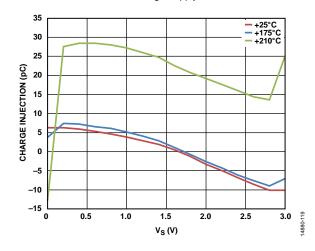


Figure 20. Charge Injection as a Function of V_S (V_D) for Various Temperatures, 3.3 V Single Supply

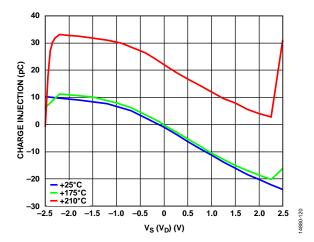
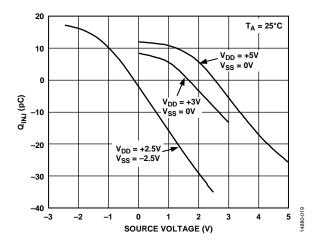
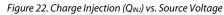


Figure 21. Charge Injection as a Function of V_S (V_D) for Various Temperatures, ±2.5 V Dual Supply





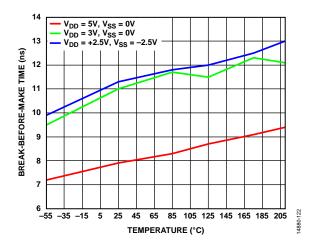
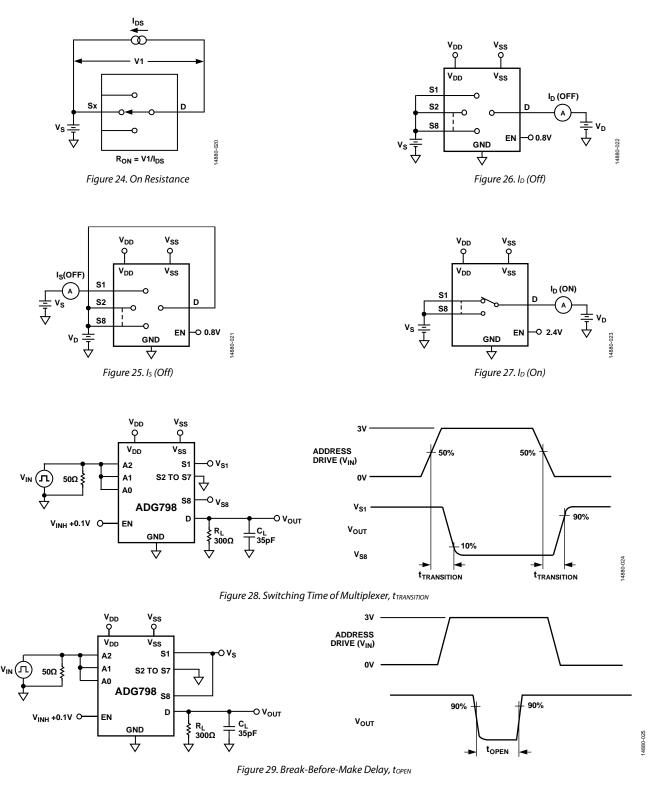
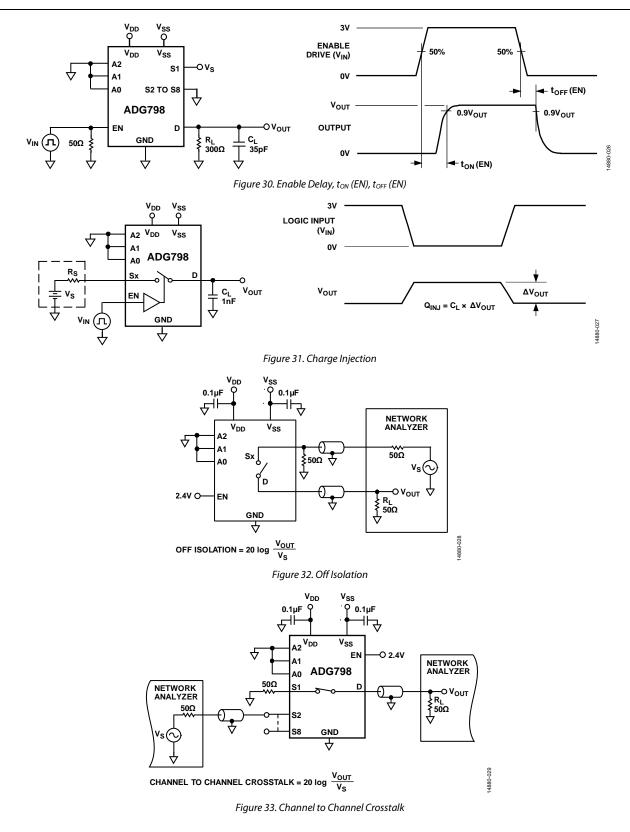


Figure 23. Break-Before-Make Time vs. Temperature

TEST CIRCUITS





Data Sheet

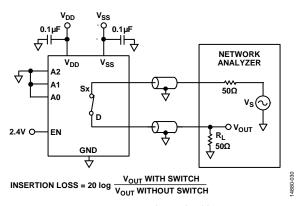


Figure 34. –3 dB Bandwidth

TERMINOLOGY

VDD

 V_{DD} is the most positive power supply potential.

Vss

 V_{ss} is the most negative power supply in a dual-supply application. In single-supply applications, tie V_{ss} to ground at the device.

GND

GND is the ground (0 V) reference.

Sx

Sx are the source terminals and can be inputs or outputs.

D

D is the drain terminal and can be an input or an output.

Ax

Ax is the logic control input.

EN

EN is the active high enable.

Ron

 $R_{\mbox{\scriptsize ON}}$ is the ohmic resistance between D and Sx.

R_{FLAT} (ON)

 $R_{\rm FLAT\,(ON)}$ flatness is the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

Is (Off)

 $I_{\text{S}}\left(\text{Off}\right)$ is the source leakage current with the switch off.

I_D (Off)

 $I_{\rm D}$ (Off) is the drain leakage current with the switch off.

 I_{D} , I_{S} (On) I_{D} , I_{S} (On) is the channel leakage current with the switch on.

 V_D (Vs) V_D (Vs) is the analog voltage on Terminal D and Terminal Sx.

Cs (Off) Cs (Off) is the off switch source capacitance and is measured with reference to ground.

C_D (Off)

 $C_{\rm D}$ (Off) is the off switch drain capacitance and is measured with reference to ground.

$C_D, C_S(On)$

 $C_{\text{D}},\,C_{\text{S}}$ (On) is the on switch capacitance and is measured with reference to ground.

CIN

 C_{IN} is the digital input capacitance.

t_{TRANSITION}

 $t_{\text{TRANSITION}}$ is the delay time measured between the 50% and 90% points of the digital inputs and the switch on condition when switching from one address state to another.

ton (EN)

 $t_{\rm ON}$ (EN) is the delay time between the 50% and 90% points of the EN digital input and the switch on condition.

toff (EN)

 t_{OFF} (EN) is the delay time between the 50% and 90% points of the EN digital input and the switch off condition.

topen

 $t_{\rm OPEN}$ is the off time measured between the 80% points of both switches when switching from one address state to another.

Off Isolation

Off isolation is a measure of unwanted signal coupling through an off switch.

Channel to Channel Crosstalk

Channel to channel crosstalk is a measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Charge Injection

Charge injection is a measure of the glitch impulse transferred from injection of the digital input to the analog output during switching.

-3 dB Bandwidth

-3 dB bandwidth is the frequency at which the output is attenuated by 3 dB.

On Response

On response is the frequency response of the on switch.

On Loss On loss is the loss due to the on resistance of the switch.

 V_{INL} V_{INL} is the maximum input voltage for Logic 0.

V_{INH}

 $V_{\mbox{\scriptsize INH}}$ is the minimum input voltage for Logic 1.

$\label{eq:IINL} \begin{array}{l} I_{INL} \left(I_{INH} \right) \\ I_{INL} \left(I_{INH} \right) \text{ is the input current of the digital input.} \end{array}$

 I_{DD} I_{DD} is the positive supply current.

Iss Legist

Iss is the negative supply current.

THEORY OF OPERATION

The ADG798 is a bidirectional, 8:1 CMOS multiplexer designed for very high temperature operation. The device is controlled by four parallel digital inputs (EN, A0, A1, and A2). The EN input allows the ADG798 to be enabled or disabled. When the ADG798 is disabled, the source pins (S1 to S8) disconnect from the drain pin (D). When the ADG798 is enabled, the address lines (A0, A1, and A2) can determine which source pin (S1 to S8) is connected to the drain pin (D).

The low on resistance and on-resistance flatness of this device means that there is minimal signal distortion across the entire signal range of the device. This minimal signal distortion, combined with the close on-resistance match between channels, makes this device ideal for applications where the error due to on resistance is key. The ADG798 also exhibits extremely fast switching times and extremely low power consumption, making the device useful in applications where there is a tight power budget. The ADG798 is compatible with single-supply systems that have a $V_{\rm DD}$ range from 5.5 V to 3.3 V and dual-supply systems at ± 2.5 V.

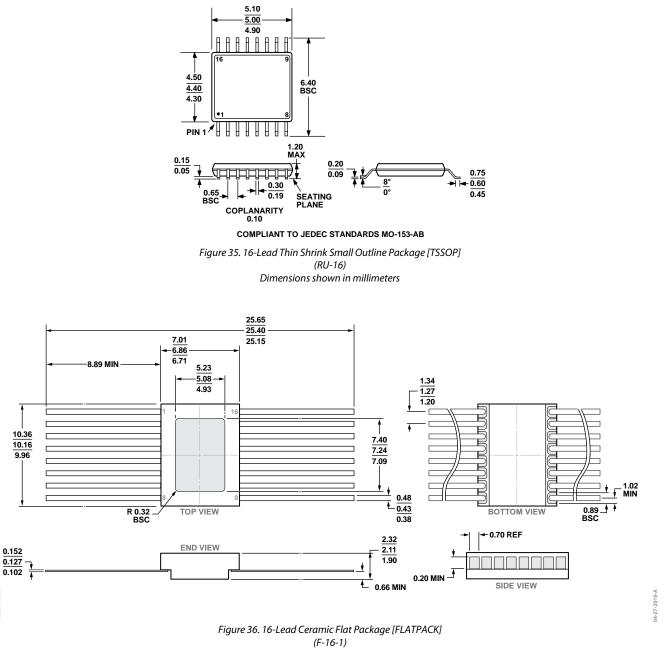
The ADG798 operates in a wide ambient temperature range from -55°C to +210°C (FLATPACK) or -55°C to +175°C (TSSOP), making the ADG798 perfect for use in harsh environments that subject the device to extreme temperature ranges, such as downhole drilling and avionics.

APPLICATIONS INFORMATION

POWER SUPPLY SEQUENCING

When using CMOS devices, take care to ensure correct power supply sequencing. Incorrect power supply sequencing may subject the device to stresses beyond the absolute maximum ratings listed in Table 5. Always apply digital and analog inputs after power supplies and ground. For single-supply operation, tie V_{SS} to GND as close to the device as possible.

OUTLINE DIMENSIONS



Dimensions shown in millimeters

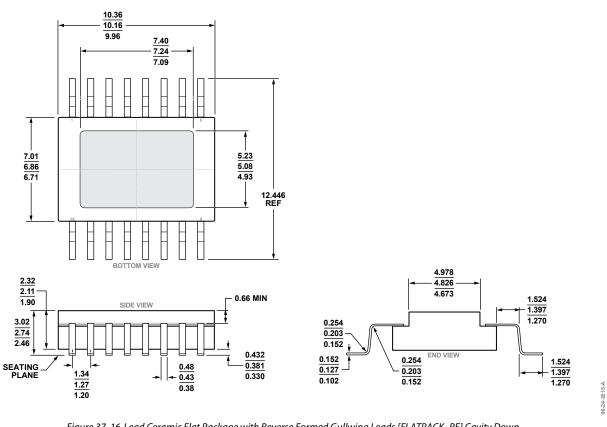


Figure 37. 16-Lead Ceramic Flat Package with Reverse Formed Gullwing Leads [FLATPACK_RF] Cavity Down (FR-16-1) Dimensions shown in millimeters

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
ADG798HRUZ	–55°C to +175°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG798HFZ	-55°C to +210°C	16-Lead Ceramic Flat Package [FLATPACK]	F-16-1
ADG798HFRZ	–55°C to +210°C	16-Lead Ceramic Flat Package [FLATPACK_RF]	FR-16-1
EVAL-ADG798EB1Z		Evaluation Board	

 1 Z = RoHS Compliant Part.

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